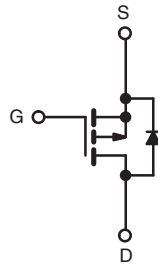
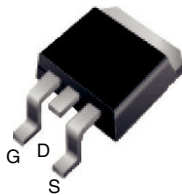


## Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	- 200	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = - 10$ V	3
$Q_g$ (Max.) (nC)	11	
$Q_{gs}$ (nC)	7	
$Q_{gd}$ (nC)	4	
Configuration	Single	

**D<sup>2</sup>PAK (TO-263)**


P-Channel MOSFET

### FEATURES

- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- P-Channel
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS\***  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### Note

\* Lead (Pb)-containing terminations are not RoHS-compliant. Exemptions may apply.

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D<sup>2</sup>PAK (TO-263) is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>PAK (TO-263) is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2 W in a typical surface mount application.

ORDERING INFORMATION	
Package	D <sup>2</sup> PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHF9610S-GE3
	SiHF9610STRR-GE3
	SiHF9610STRL-GE3
Lead (Pb)-free	IRF9610SPbF
	SiHF9610S-E3
	IRF9610STRRPbF
	IRF9610STRLPbF

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			$V_{DS}$	- 200	V
Gate-Source Voltage			$V_{GS}$	$\pm 20$	
Continuous Drain Current	$V_{GS}$ at - 10 V	$T_C = 25$ °C	$I_D$	- 1.8	A
		$T_C = 100$ °C		- 1	
Pulsed Drain Current <sup>a</sup>			$I_{DM}$	- 7	W/°C
Linear Derating Factor				0.16	
Linear Derating Factor (PCB Mount) <sup>d</sup>				0.025	
Maximum Power Dissipation	$T_C = 25$ °C		$P_D$	20	W
Maximum Power Dissipation (PCB Mount) <sup>d</sup>	$T_A = 25$ °C			3	
Peak Diode Recovery dV/dt <sup>b</sup>			dV/dt	- 5	V/ns
Operating Junction and Storage Temperature Range			$T_J, T_{stg}$	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300°	

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 5).
- $I_{SD} \leq - 1.8$  A,  $di/dt \leq 70$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150$  °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Ambient (PCB Mount) <sup>a</sup>	$R_{thJA}$	-	40	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	6.4	

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0, I_D = -250\text{ }\mu\text{A}$		-200	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = -1\text{ mA}$		-	-0.23	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$		-2	-	-4	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -200\text{ V}, V_{GS} = 0\text{ V}$		-	-	-100	$\mu\text{A}$
		$V_{DS} = -160\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -0.90\text{ A}^b$	-	-	3	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = -50\text{ V}, I_D = -0.90\text{ A}^b$		0.90	-	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V},$ $V_{DS} = -25\text{ V},$ $f = 1\text{ MHz}$ , see fig. 10		-	170	-	pF
Output Capacitance	$C_{oss}$			-	50	-	
Reverse Transfer Capacitance	$C_{rss}$			-	15	-	
Total Gate Charge	$Q_g$	$V_{GS} = -10\text{ V}$	$I_D = -3.5\text{ A}, V_{DS} = -160\text{ V},$ see fig. 11 and 18 <sup>b</sup>	-	-	11	nC
Gate-Source Charge	$Q_{gs}$			-	-	7	
Gate-Drain Charge	$Q_{gd}$			-	-	4	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -100\text{ V}, I_D = -0.90\text{ A},$ $R_G = 50\text{ }\Omega, R_D = 110\text{ }\Omega$ , see fig. 17 <sup>b</sup>		-	8	-	ns
Rise Time	$t_r$			-	15	-	
Turn-Off Delay Time	$t_{d(off)}$			-	1	-	
Fall Time	$t_f$			-	8	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	$L_S$			-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p-n junction diode		-	-	-1.8	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	-7	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = -1.8\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	-5.8	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = -1.8\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	240	360	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	1.7	2.6	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 5).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

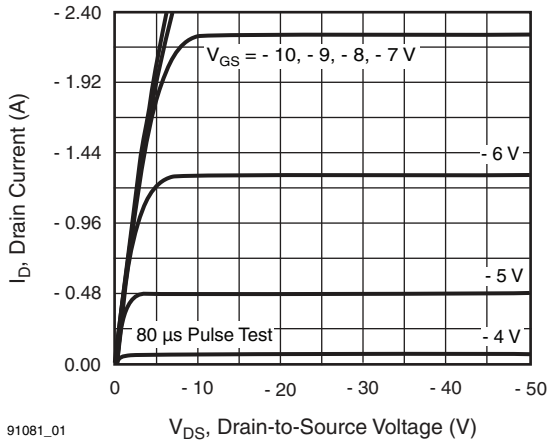


Fig. 1 - Typical Output Characteristics

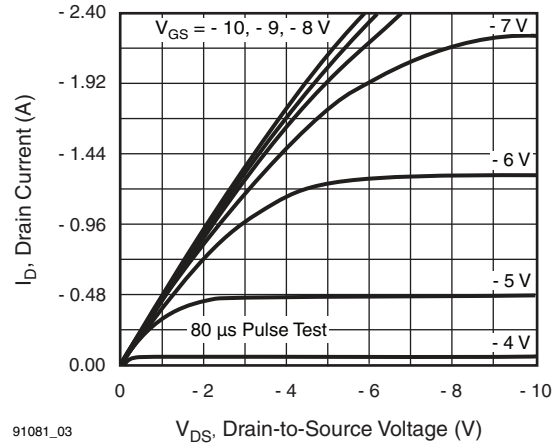


Fig. 3 - Typical Saturation Characteristics

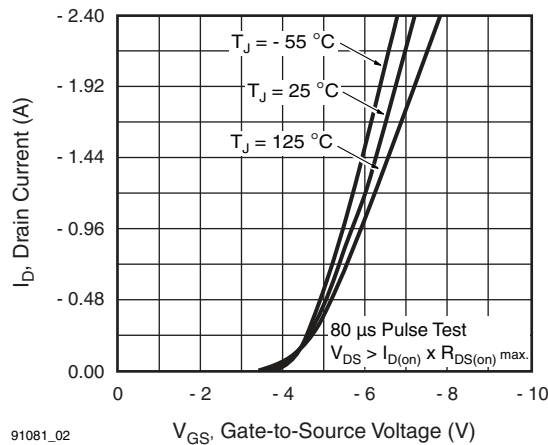


Fig. 2 - Typical Transfer Characteristics

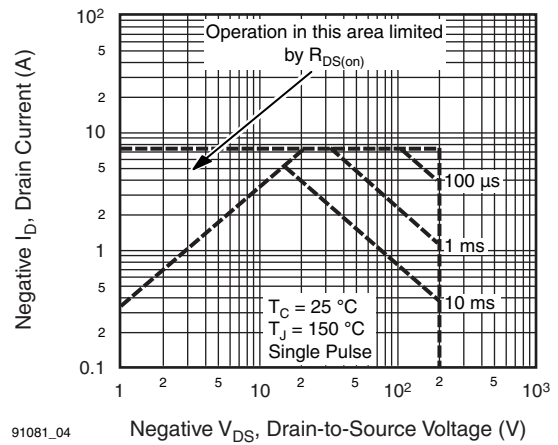


Fig. 4 - Maximum Safe Operating Area

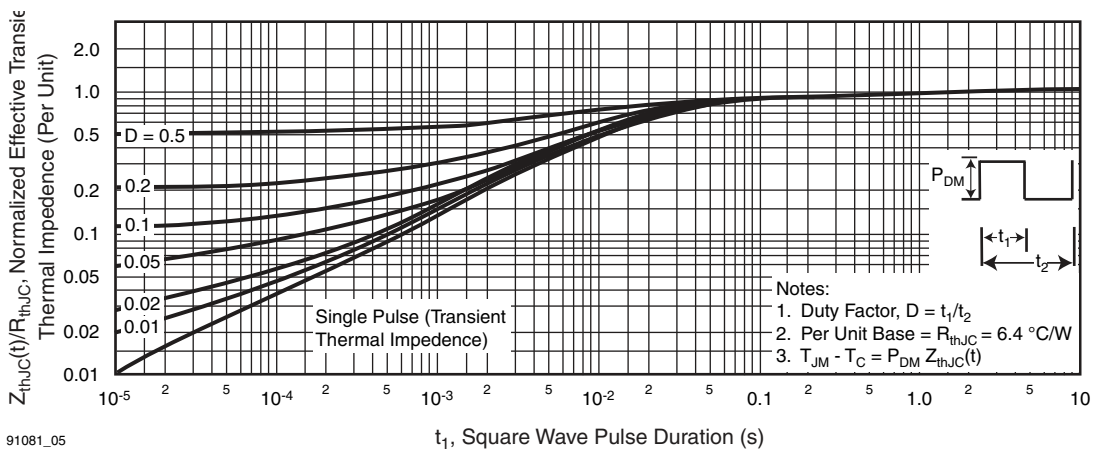
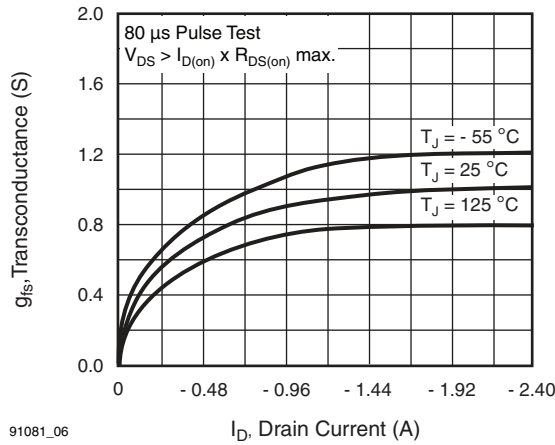
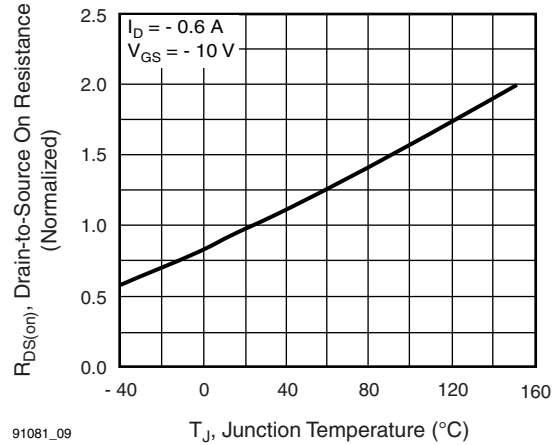


Fig. 5 - Maximum Effective Transient Thermal Impedance, Junction-to-Case vs. Pulse Duration



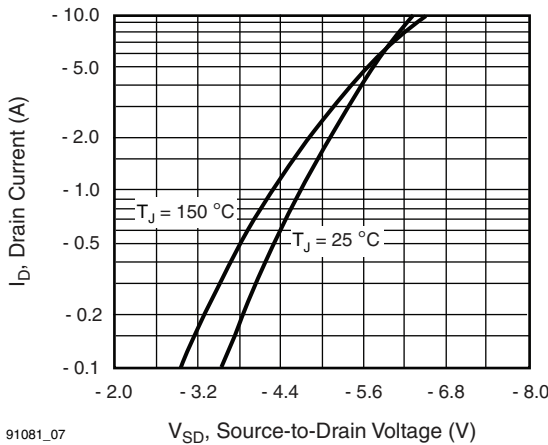
91081\_06

Fig. 6 - Typical Transconductance vs. Drain Current



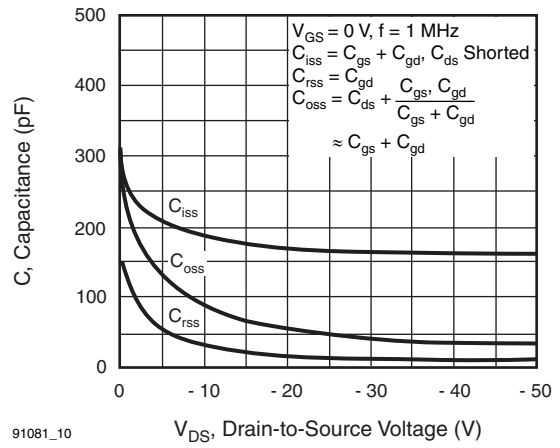
91081\_09

Fig. 9 - Normalized On-Resistance vs. Temperature



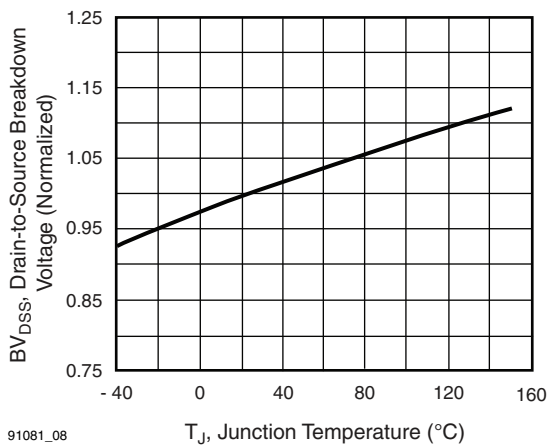
91081\_07

Fig. 7 - Typical Source-Drain Diode Forward Voltage



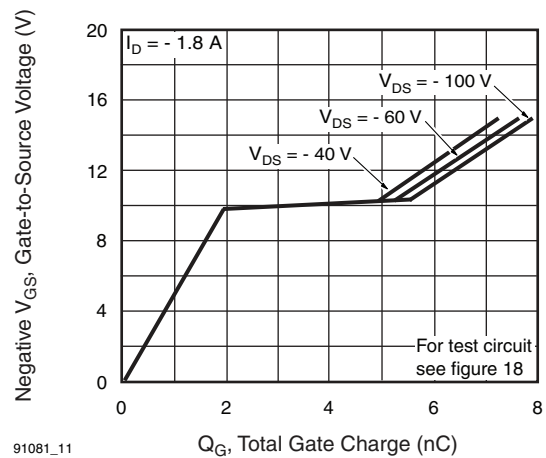
91081\_10

Fig. 10 - Typical Capacitance vs. Drain-to-Source Voltage



91081\_08

Fig. 8 - Breakdown Voltage vs. Temperature



91081\_11

Fig. 11 - Typical Gate Charge vs. Gate-to-Source Voltage

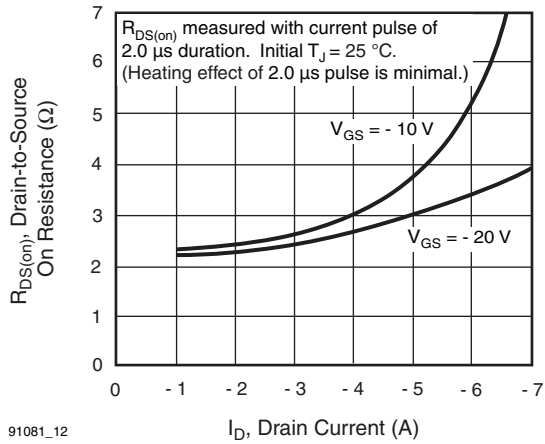


Fig. 12 - Typical On-Resistance vs. Drain Current

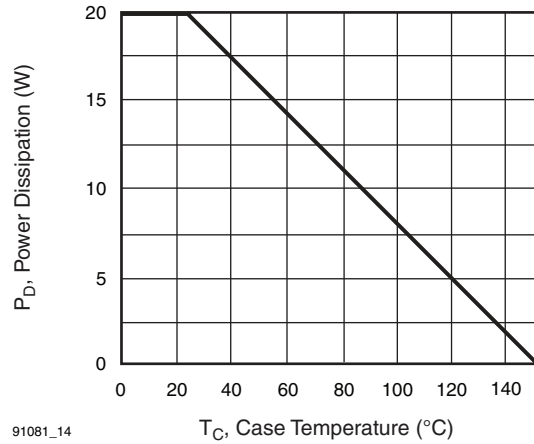


Fig. 14 - Power vs. Temperature Derating Curve

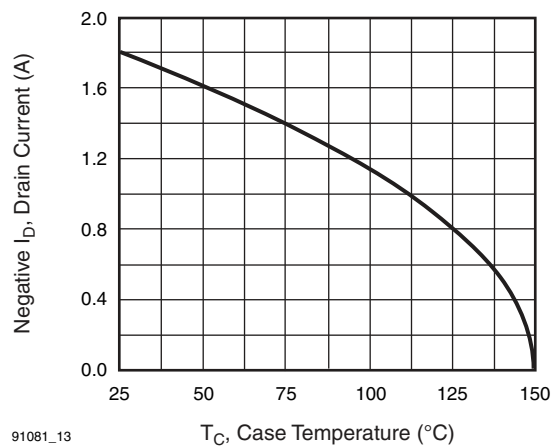


Fig. 13 - Maximum Drain Current vs. Case Temperature

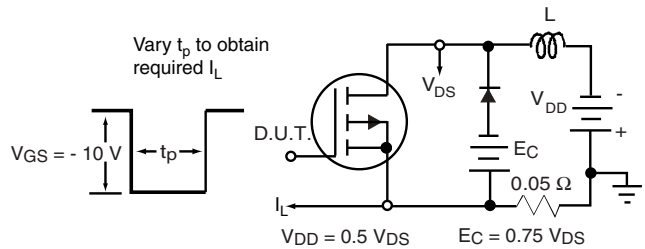


Fig. 15 - Clamped Inductive Test Circuit

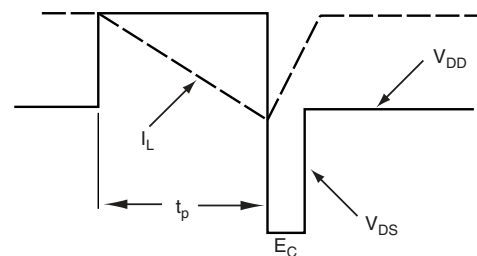


Fig. 16 - Clamped Inductive Waveforms

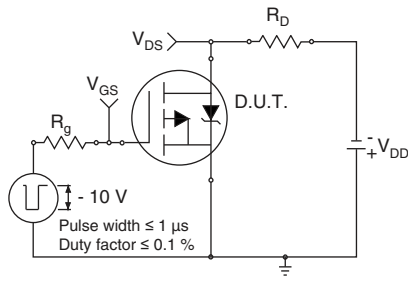


Fig. 17a - Switching Time Test Circuit

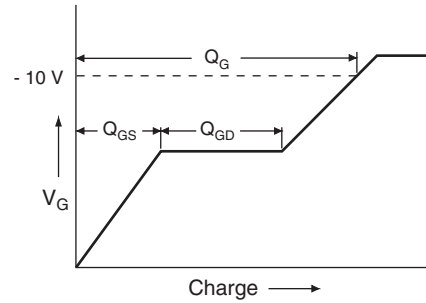


Fig. 18a - Basic Gate Charge Waveform

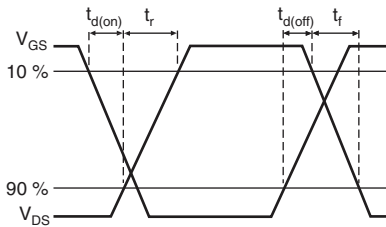


Fig. 17b - Switching Time Waveforms

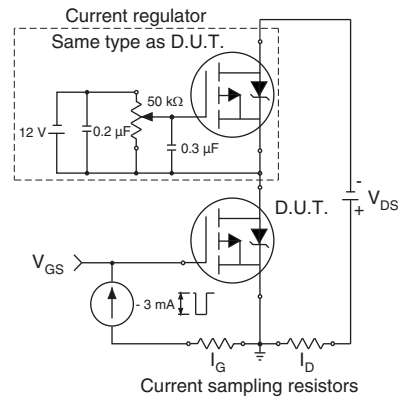
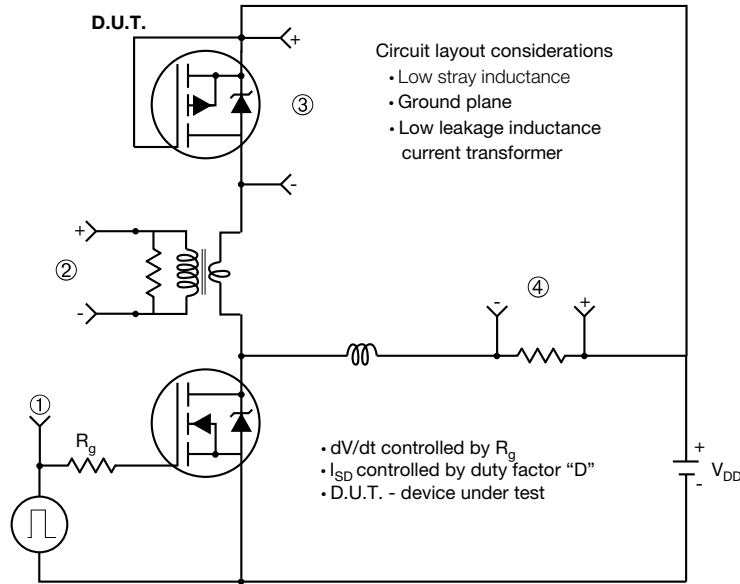


Fig. 18b - Gate Charge Test Circuit

**Peak Diode Recovery dV/dt Test Circuit**



**Note**  
• Compliment N-Channel of D.U.T. for driver



**Note**  
a.  $V_{GS} = -5\text{ V}$  for logic level and  $-3\text{ V}$  drive devices

**Fig. 19 - For P-Channel**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?91081](http://www.vishay.com/ppg?91081).

### TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08  
DWG: 5970

#### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.



**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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